

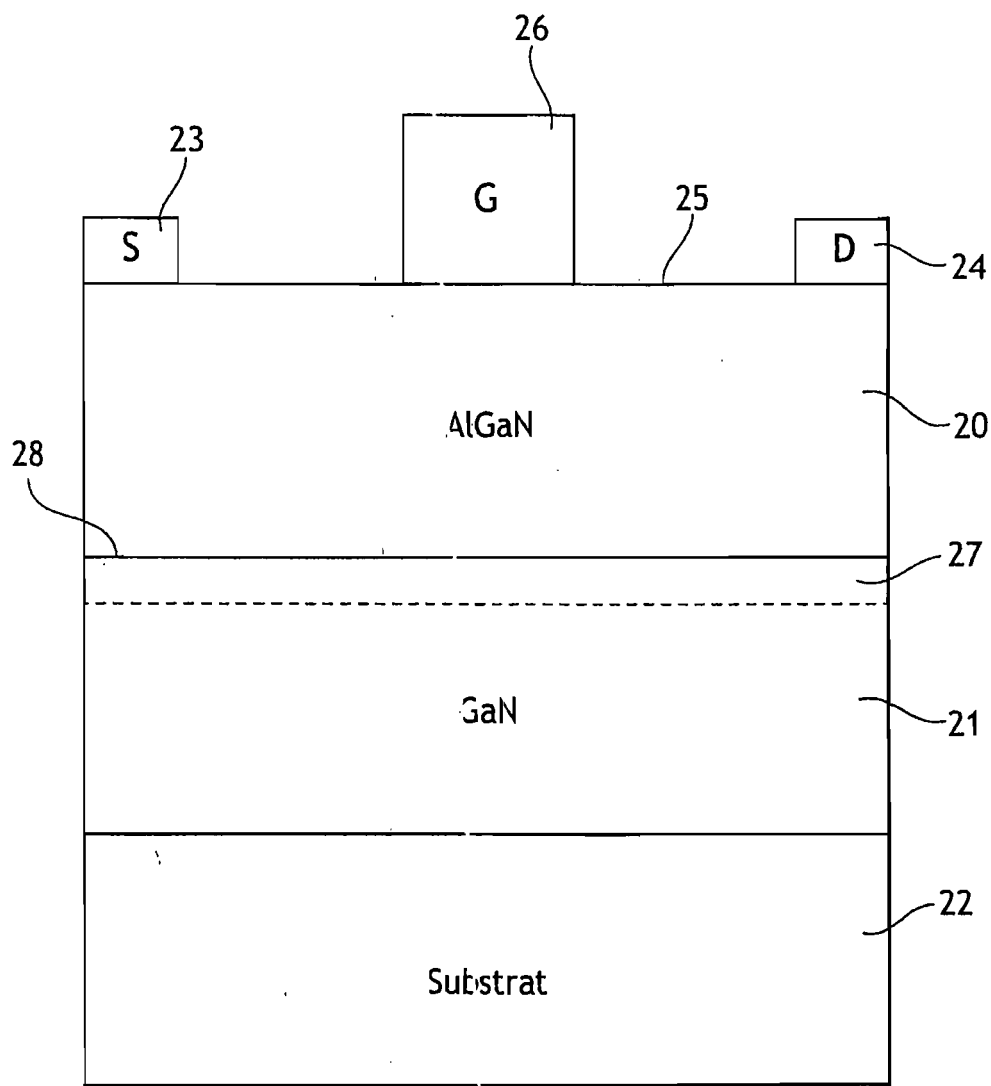


FIG.1

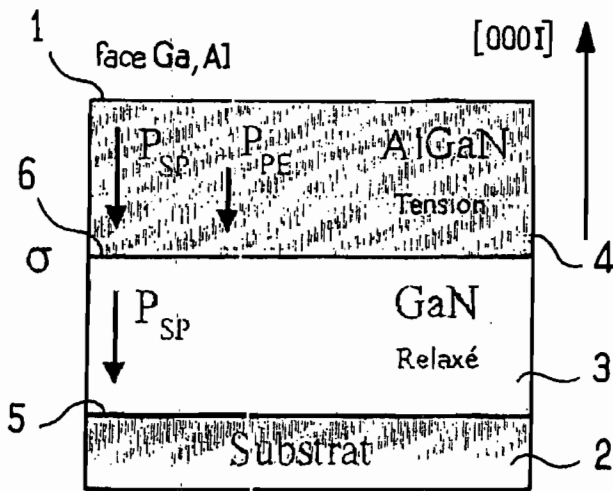


FIG.2

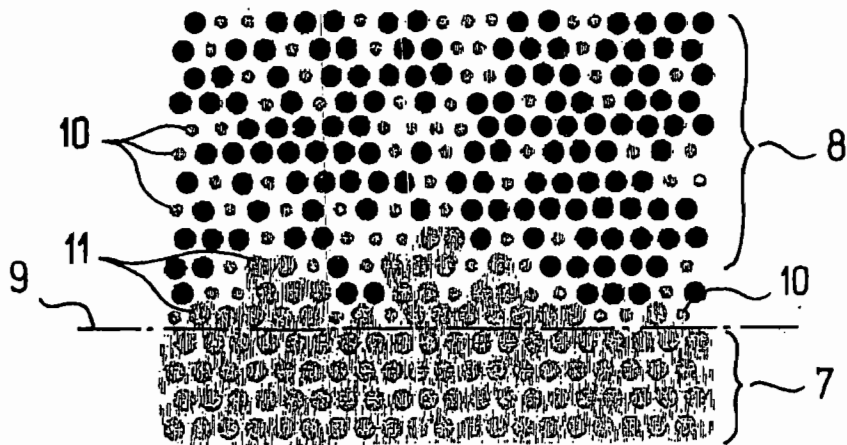


FIG.3

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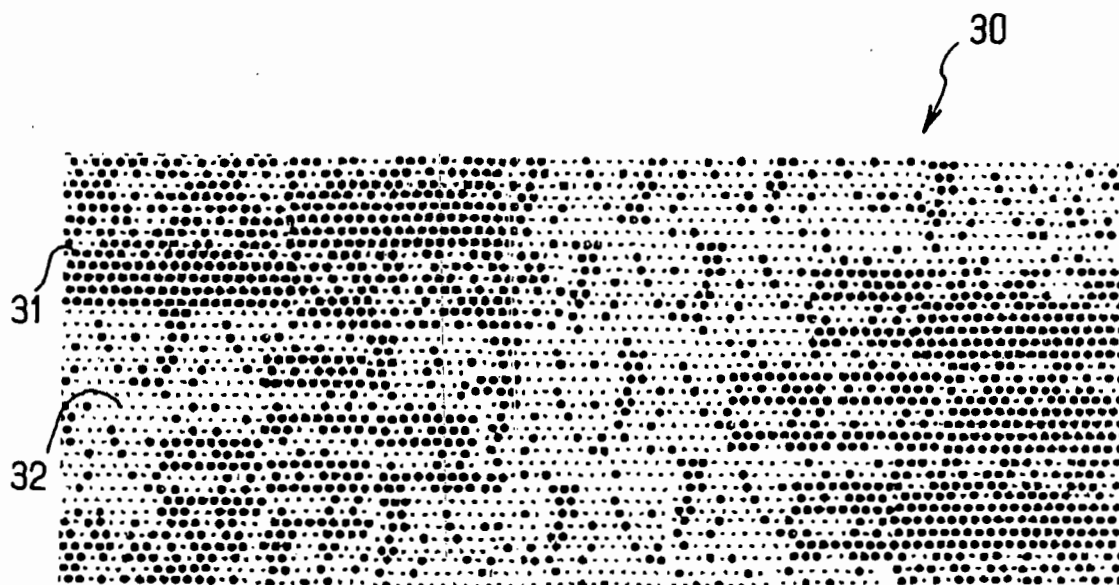


FIG. 4

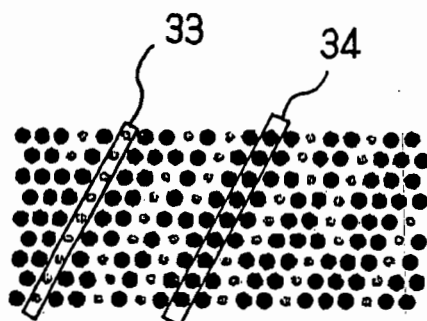


FIG. 5a

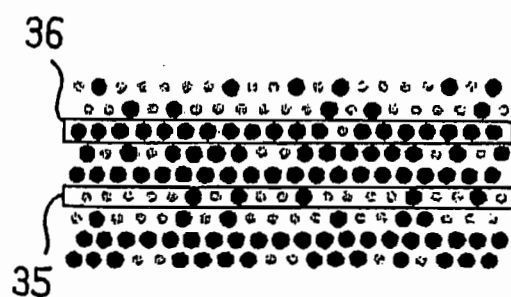


FIG. 5b

FIG.6a

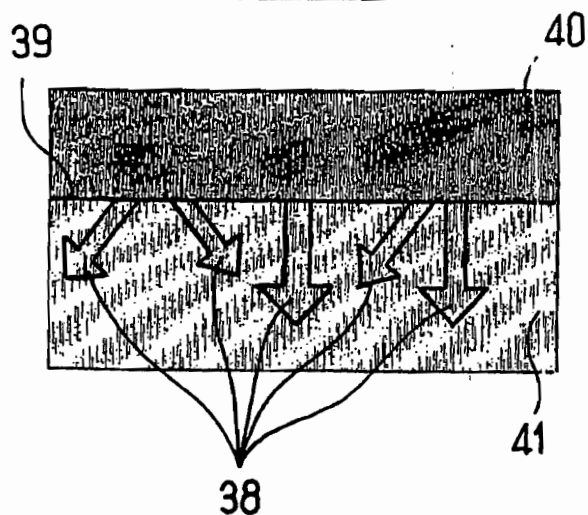


FIG.6b

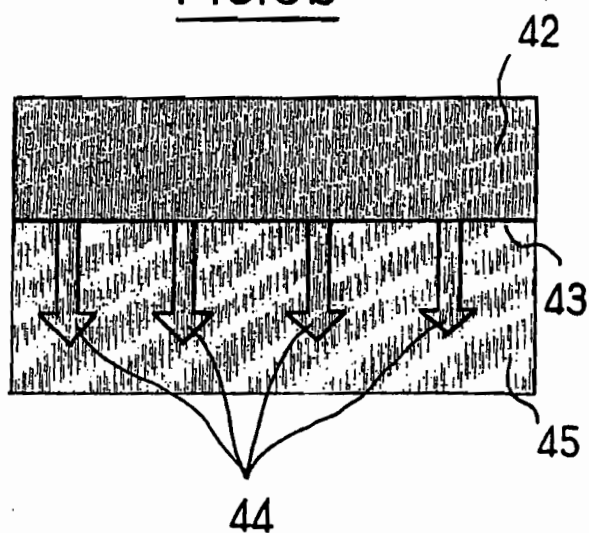
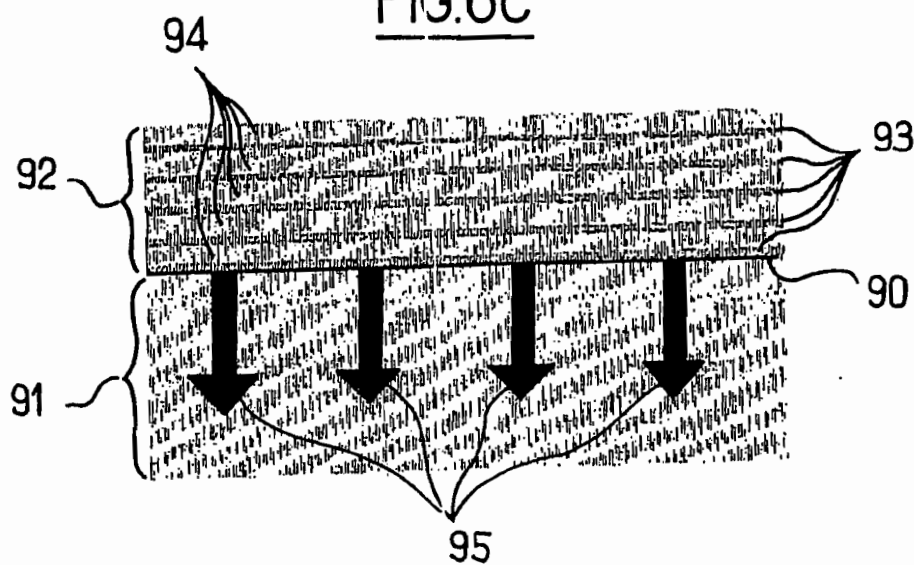


FIG.6c



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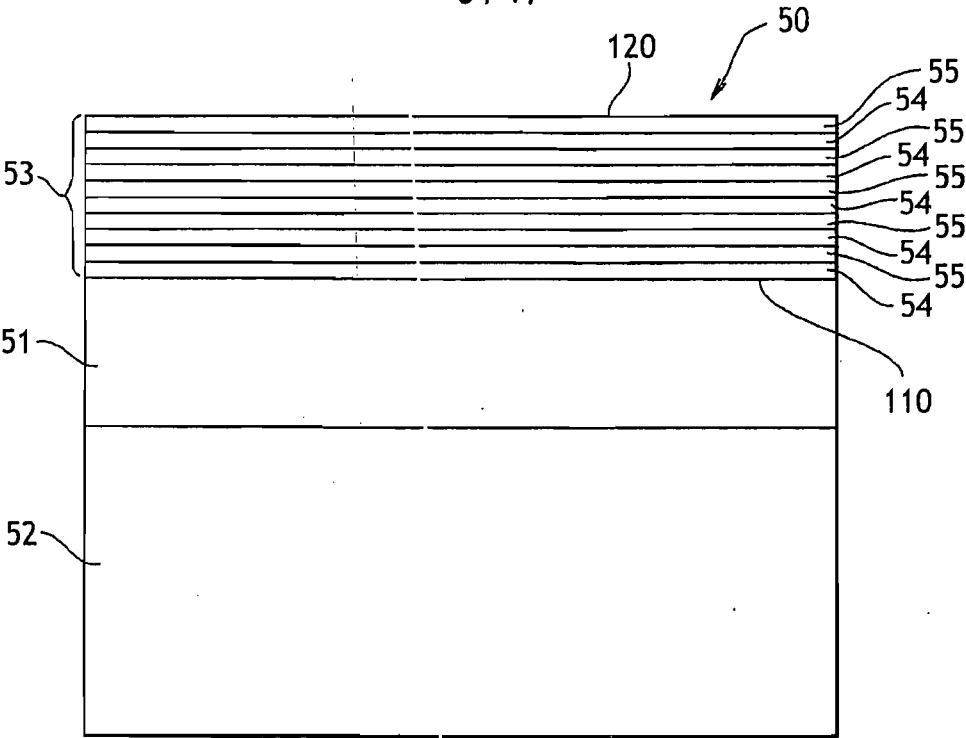


FIG. 7a

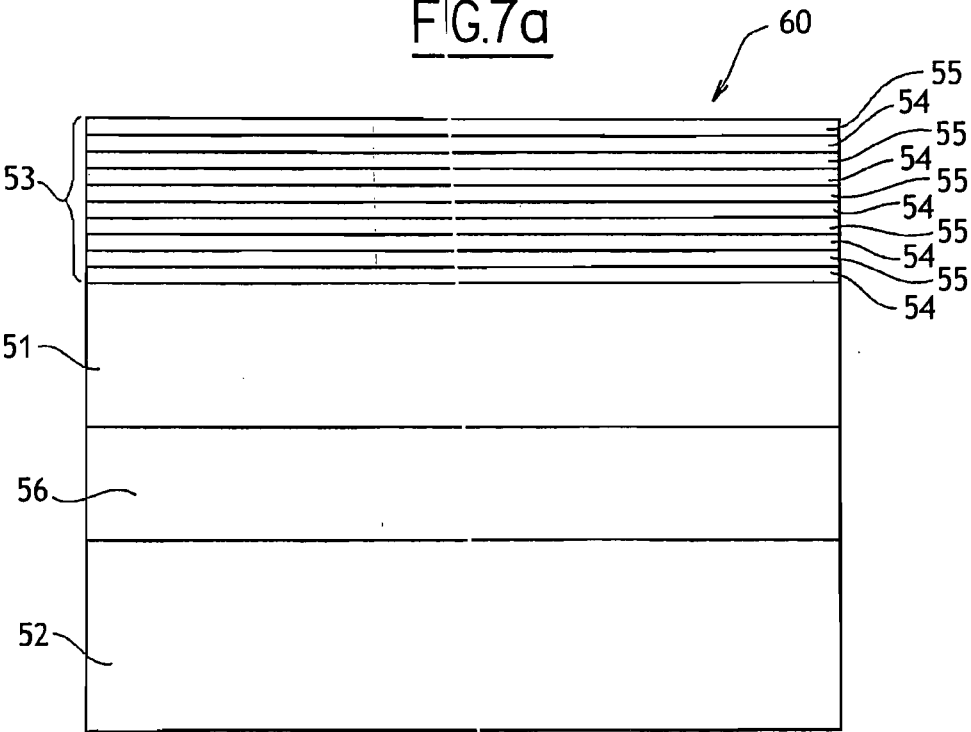


FIG. 7b

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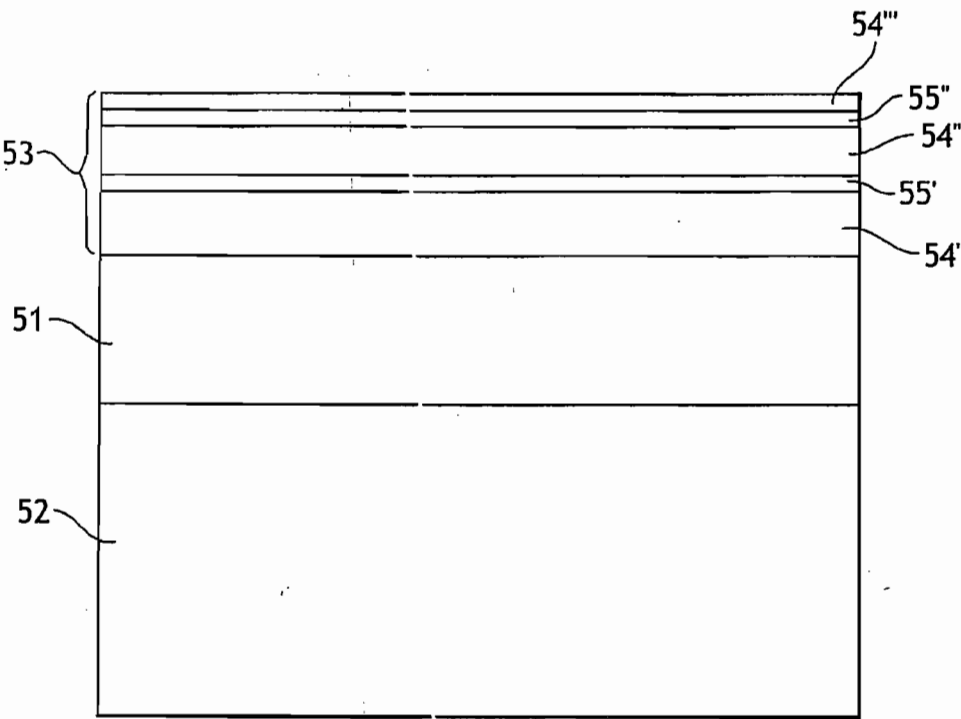


FIG.7c

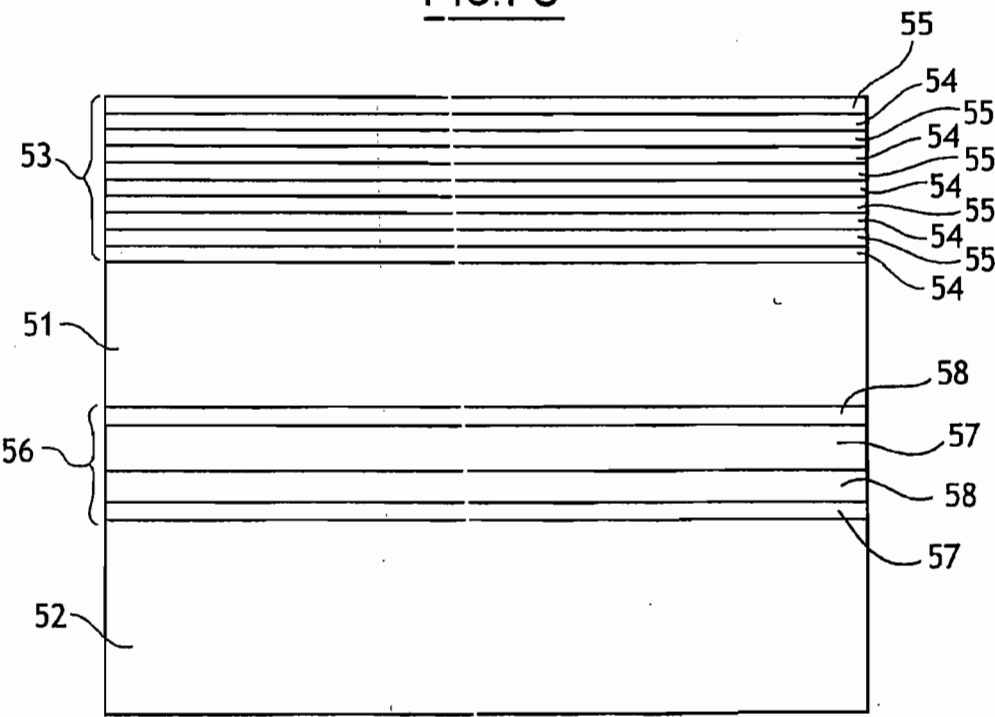


FIG.7d

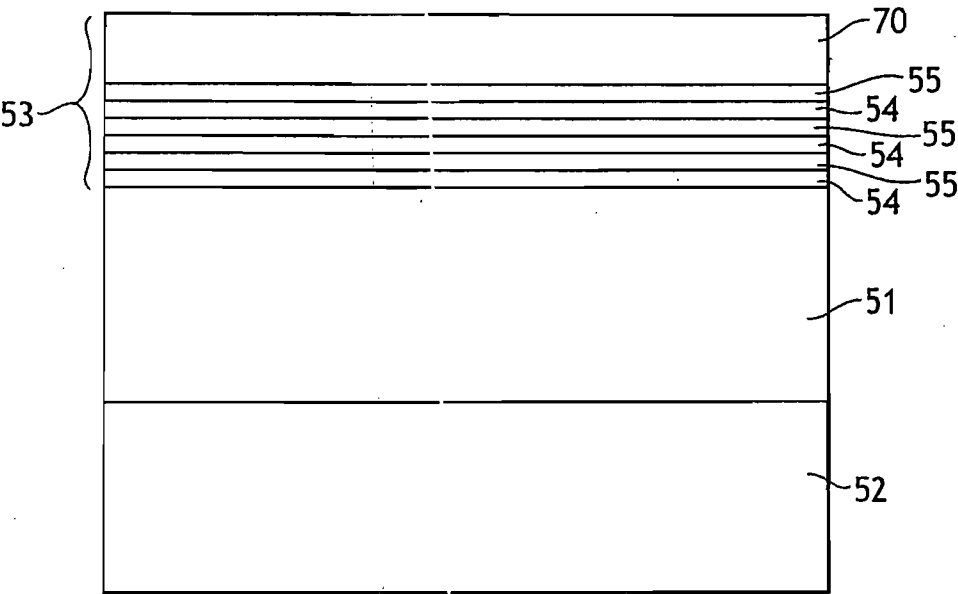


FIG. 7E

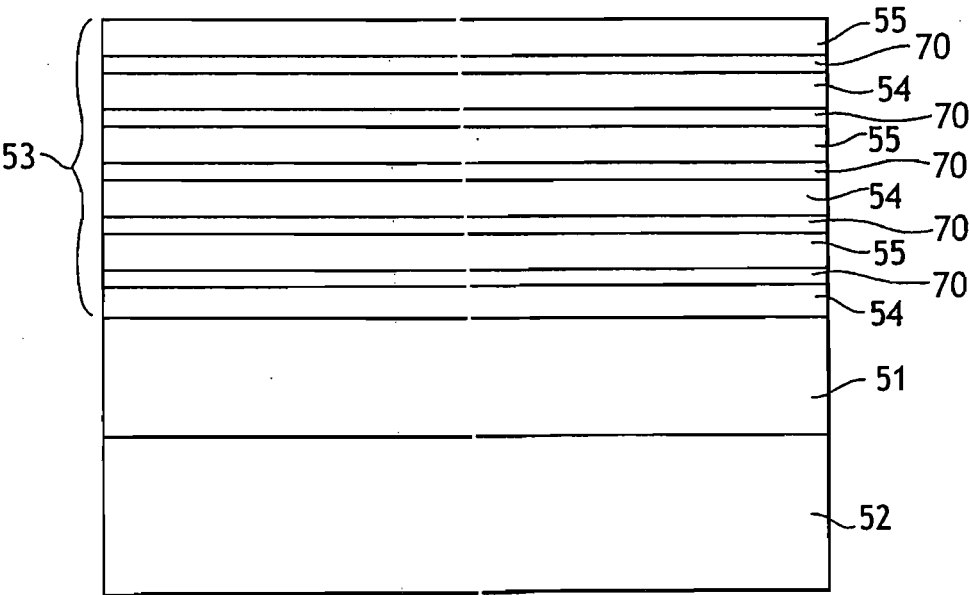


FIG. 7F

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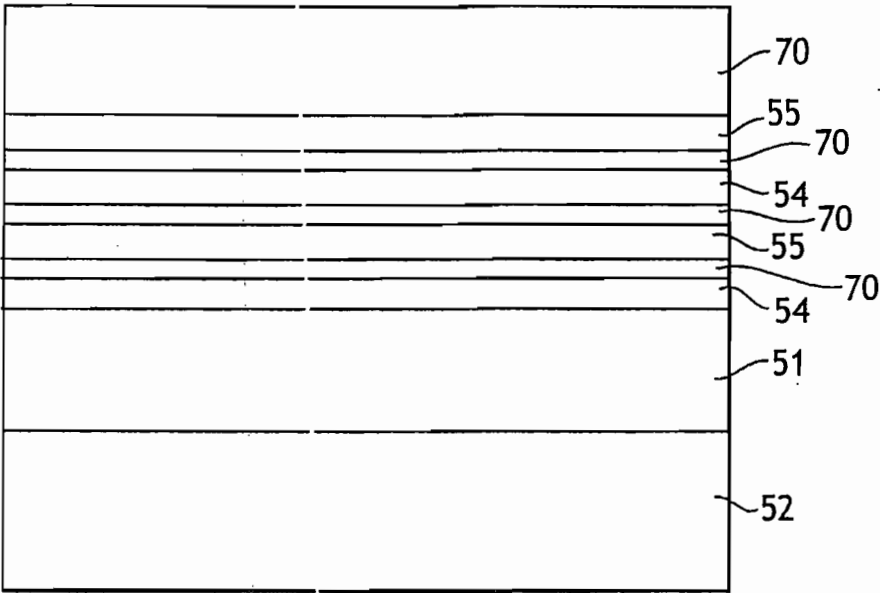


FIG. 7G

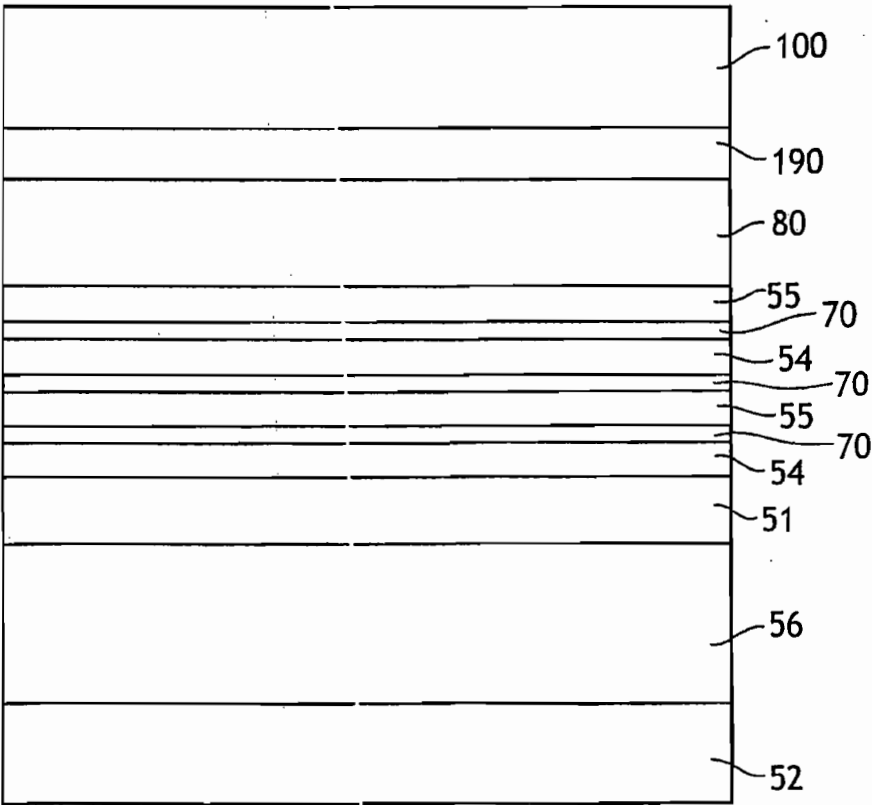


FIG. 9

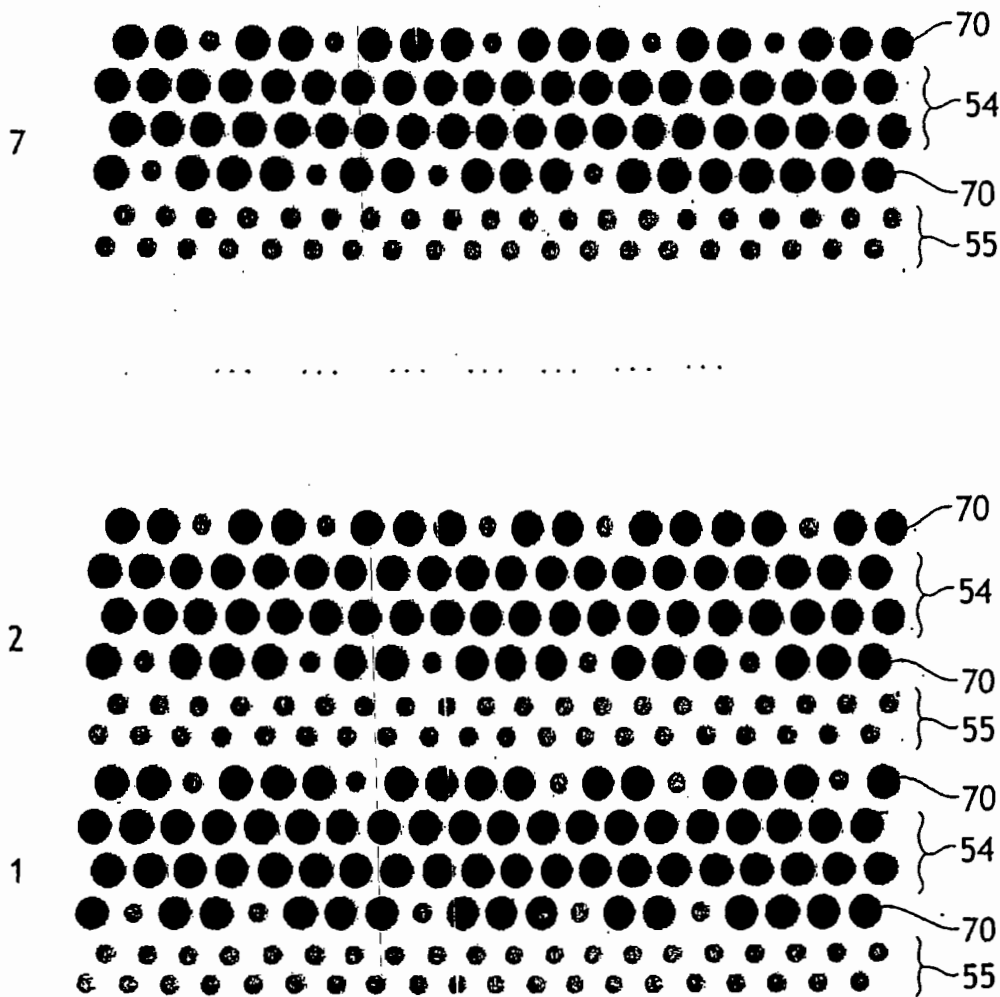


FIG.10

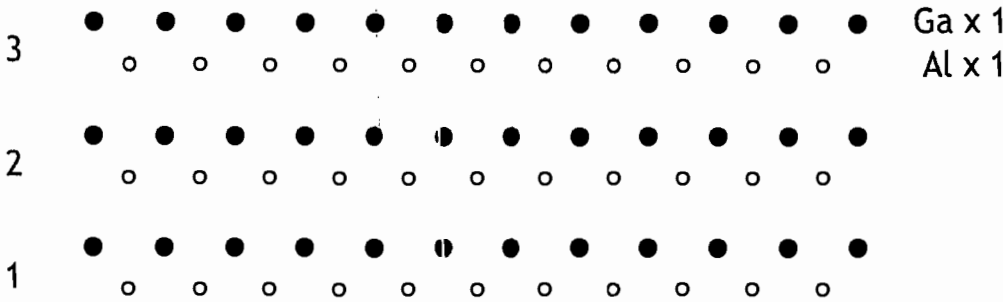


FIG. 8b

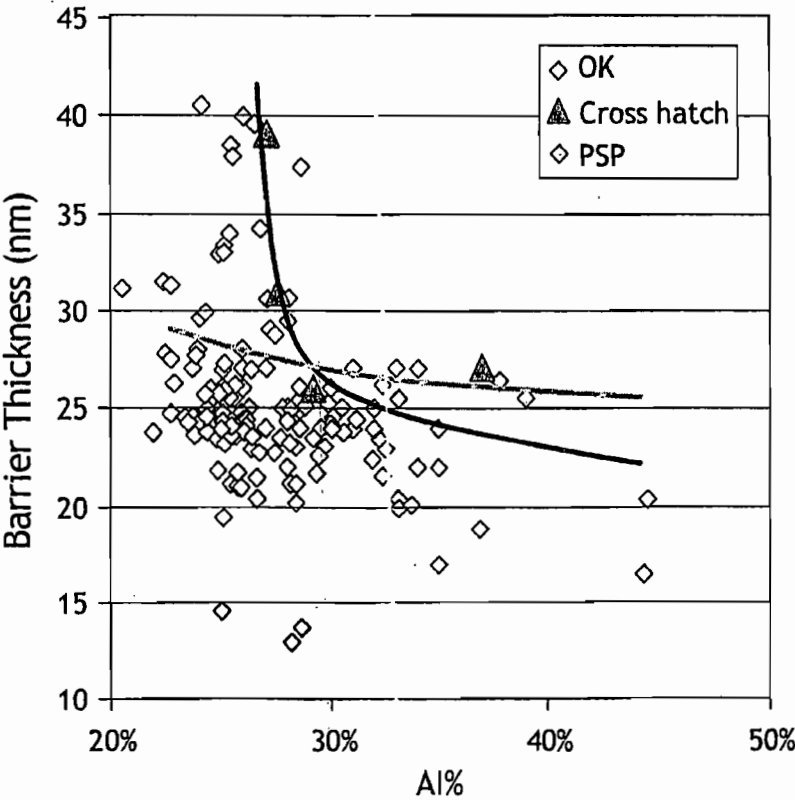


FIG. 11

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L594 (SP3 49,2% prep substrat HF+CARO+Ozone)

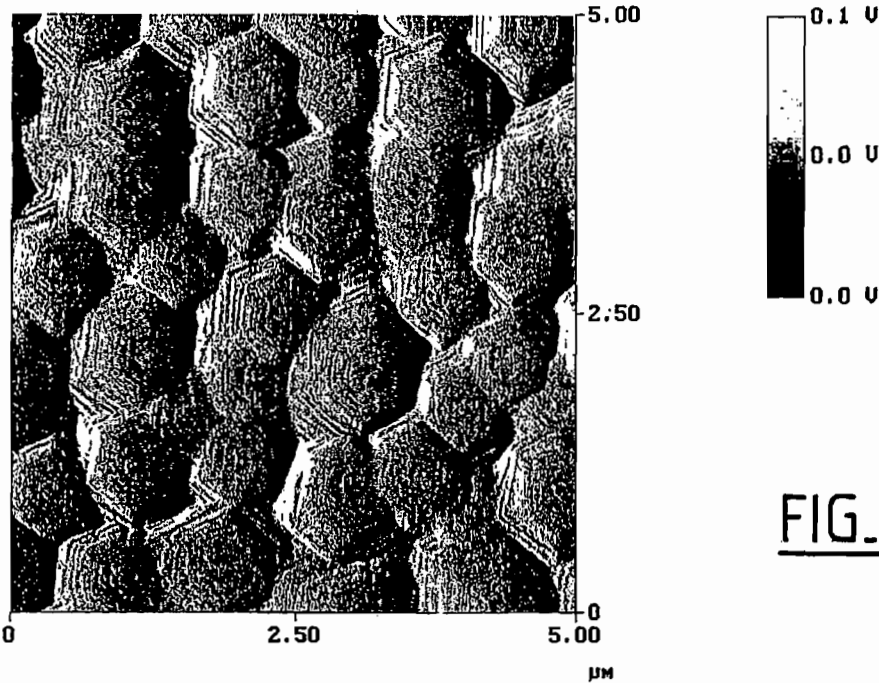


FIG.12A

Peak Surface Area Summit Zero Crossing Stopband Execute Cursor
Roughness Analysis

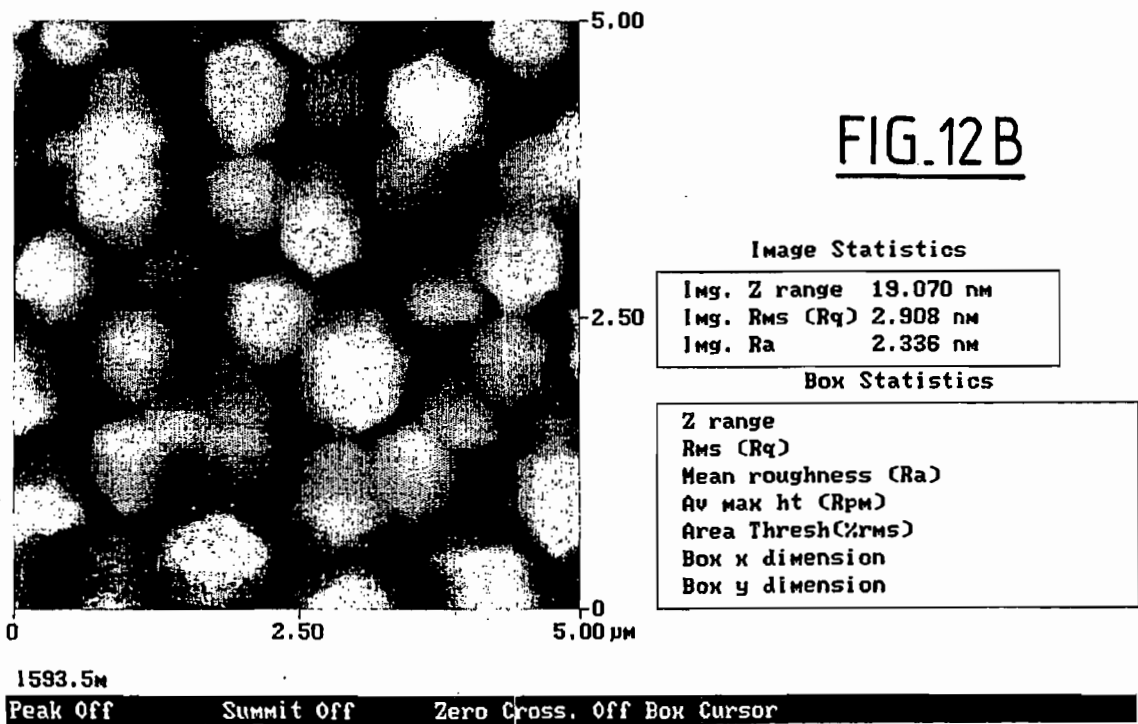


FIG.12B

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L594 (SP3 66,9% prep substrat HF+CARO)

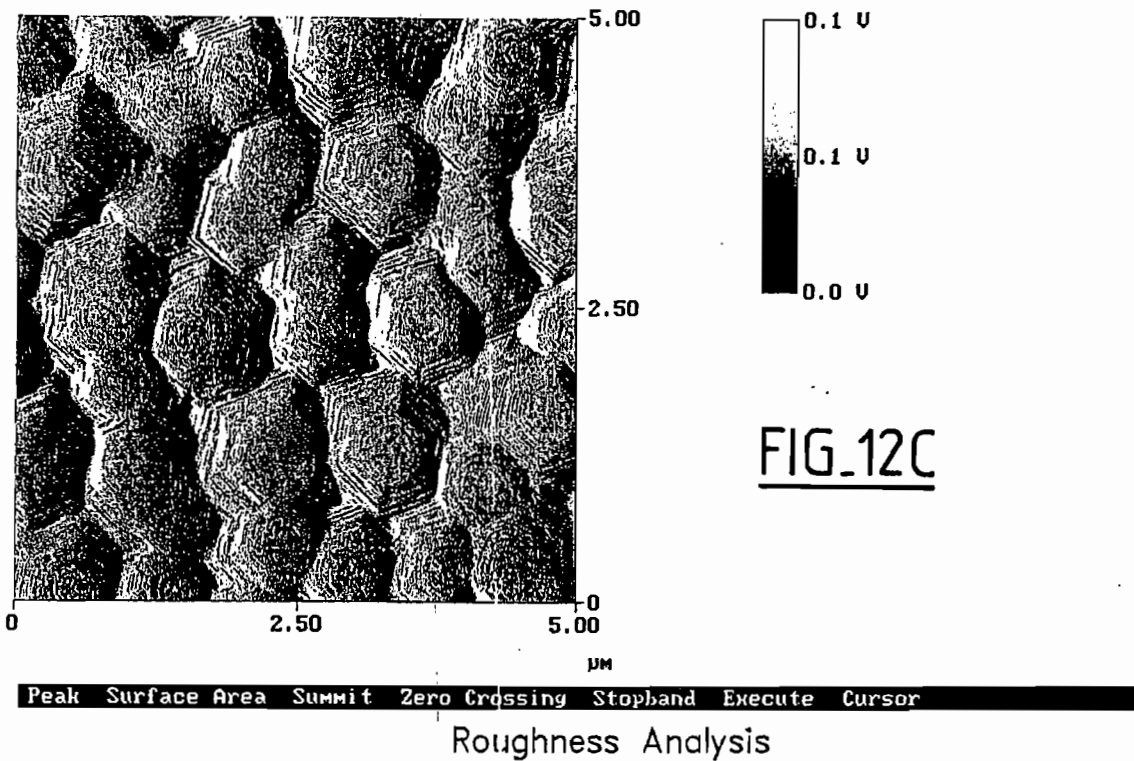


FIG.12C

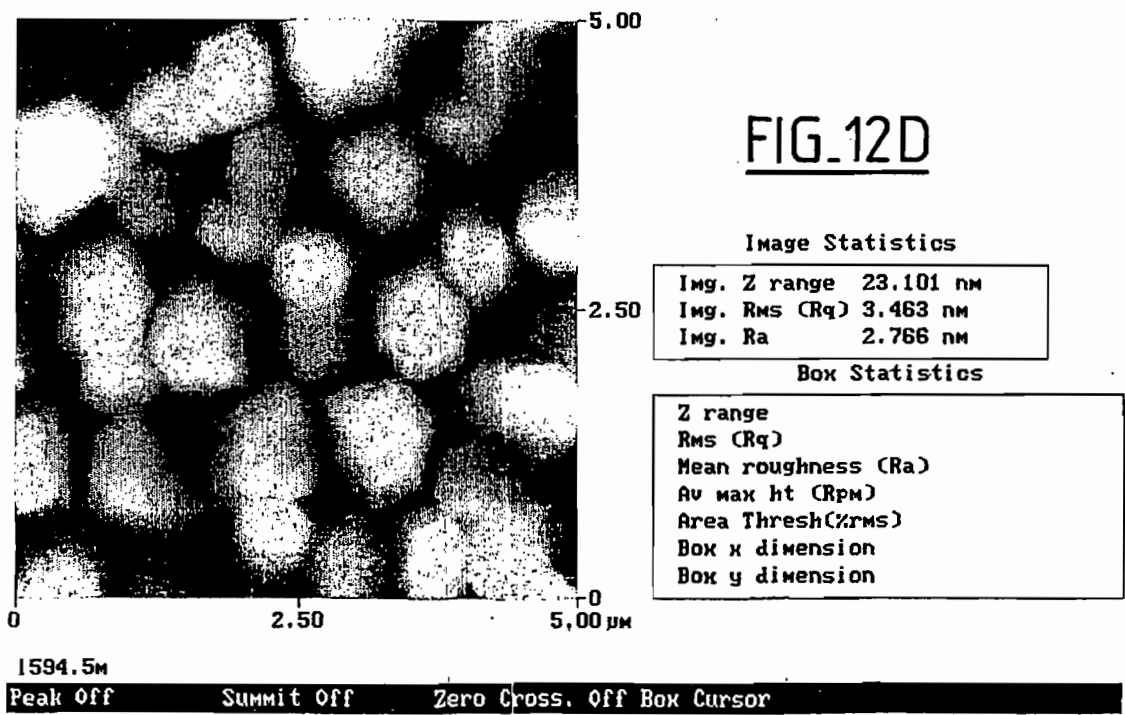
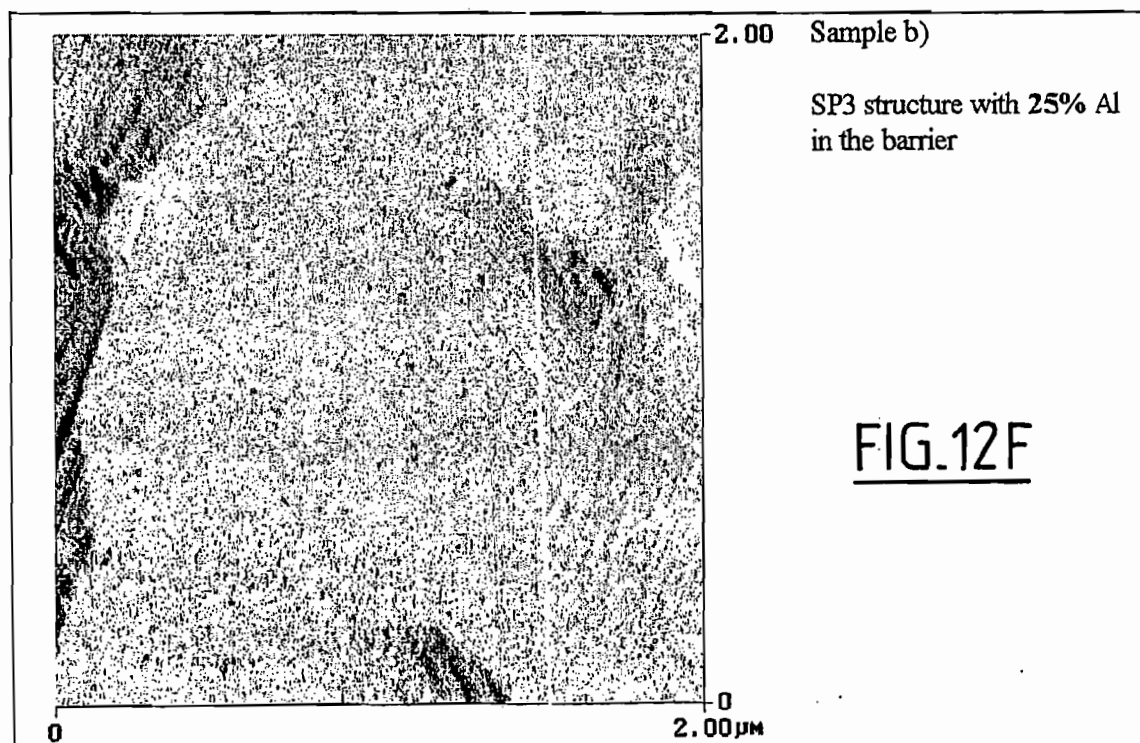
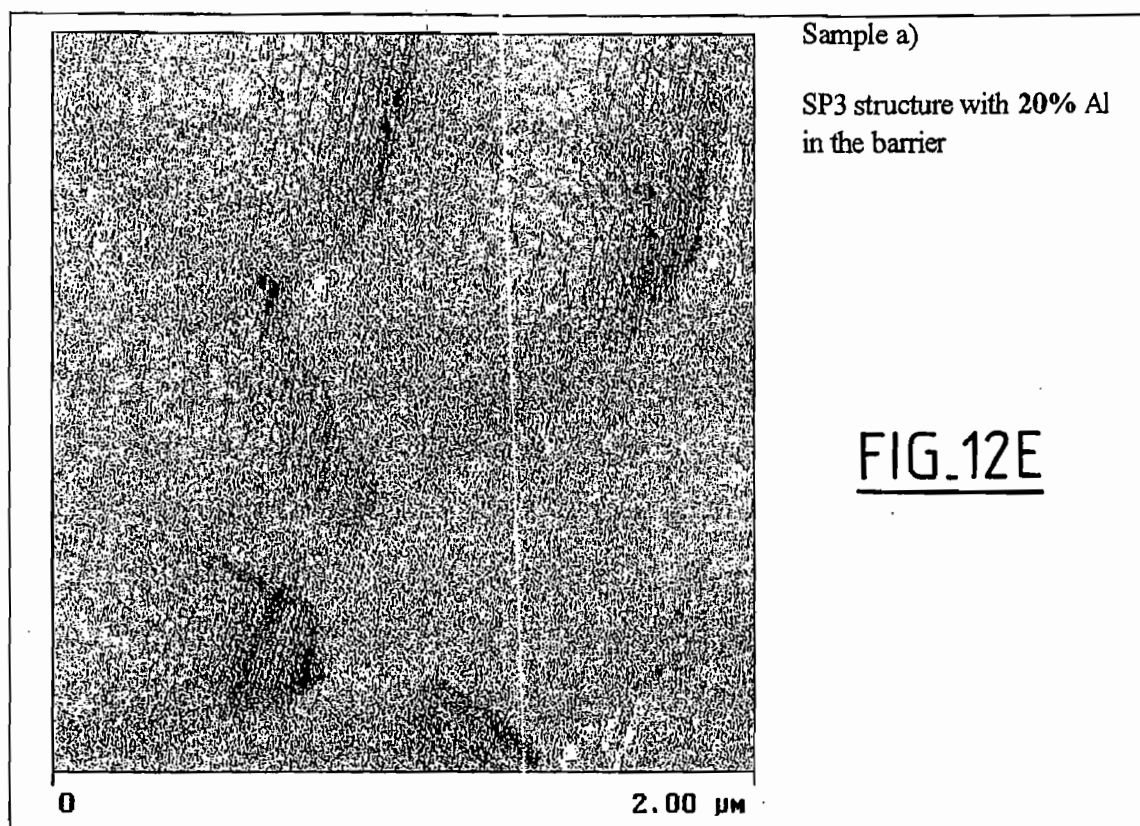
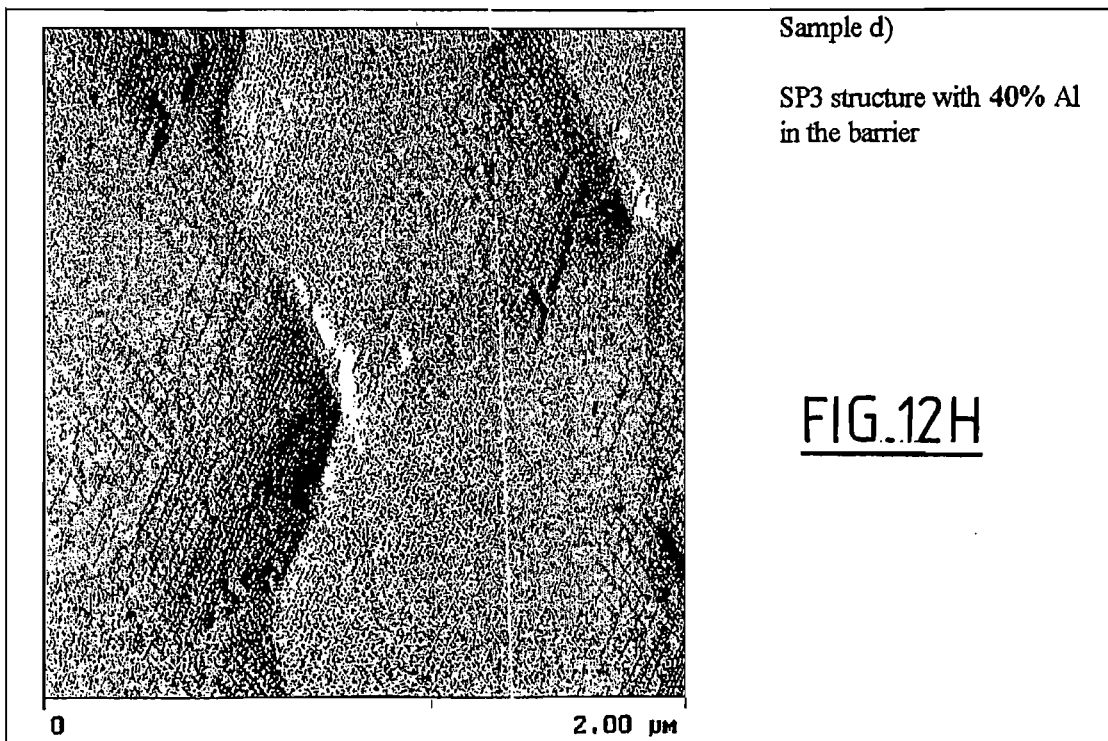
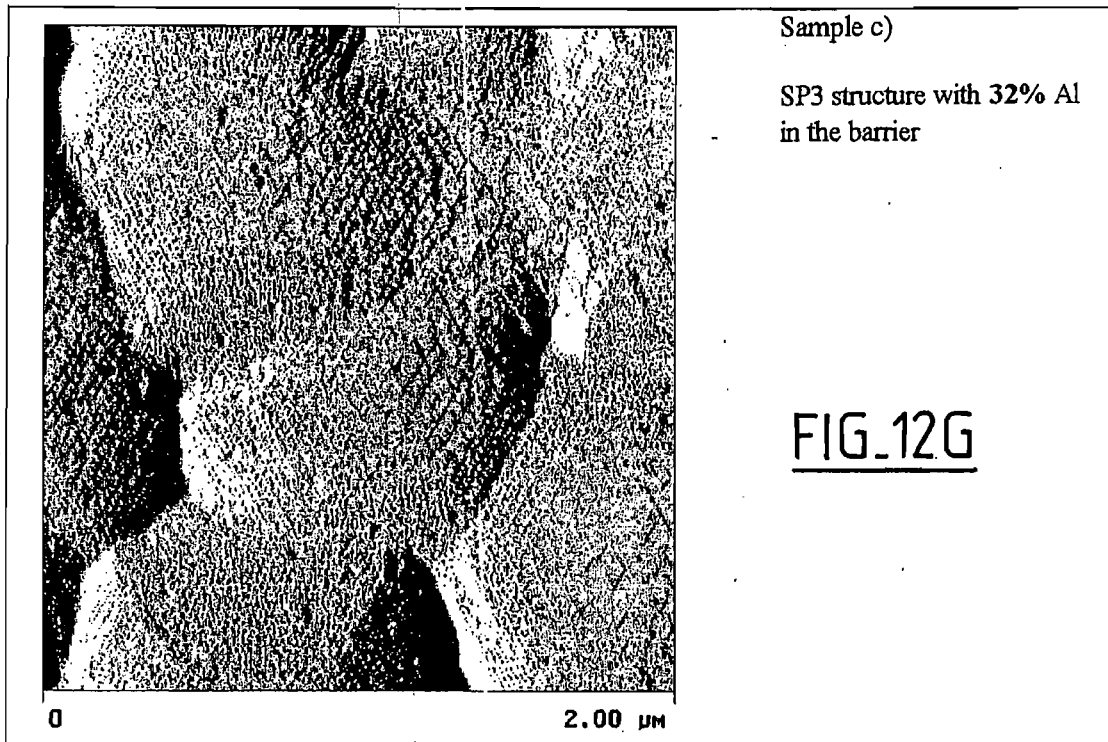


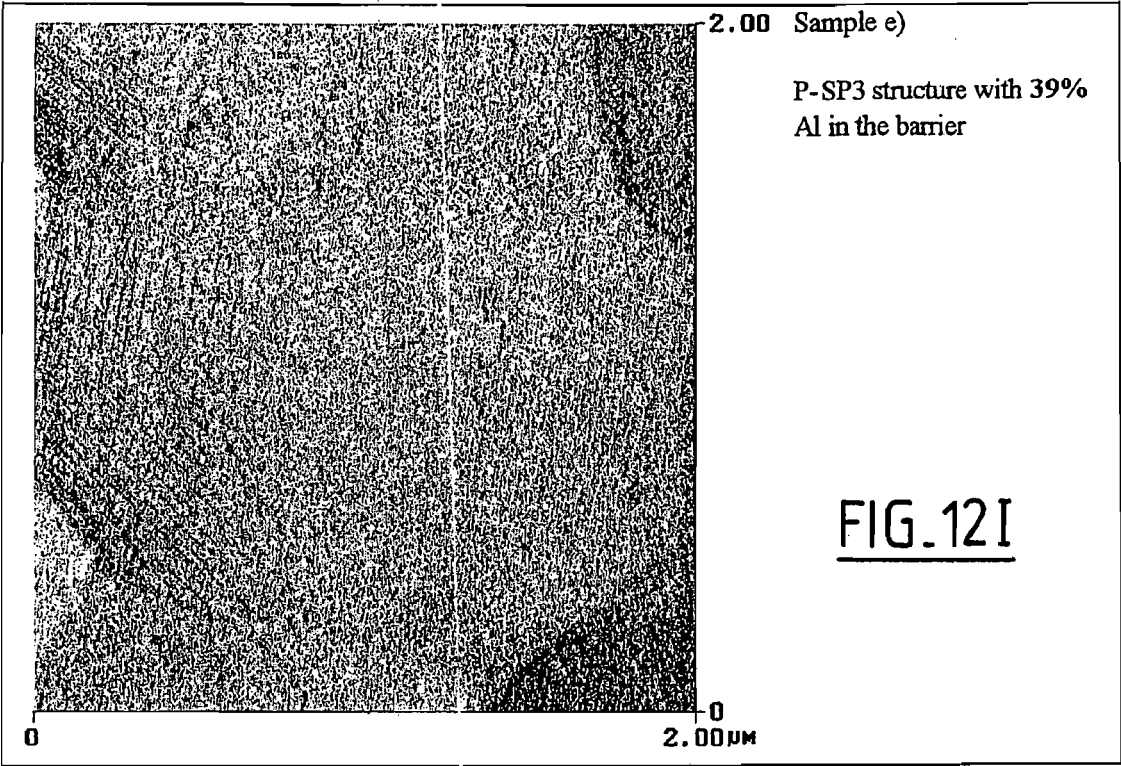
FIG.12D

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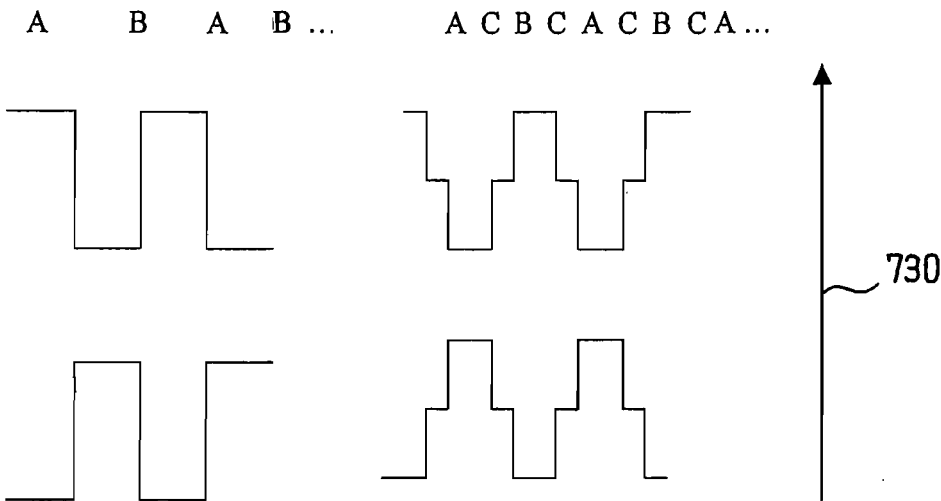




7		GaN Cap		2 nm		650
6		AlGaN Schottky layer		4 nm	25%	640
4		AlGaN Barrier		11 nm	50%	630
3		GaN channel		15 nm		620
2		AlGaN template		1500 nm	10%	610
1		PICOGIGA Buffer		500 nm		600

FIG.13

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GaN cap	
AlGaN 25%	(10 nm)
C	
Daz electrons	
GaN buffer	

X8

710

GaN cap	
AlGaN 25%	(4 nm)
C	
B	
B	
C	
A	
Daz electrons	
GaN buffer	

720

X10

FIG.14